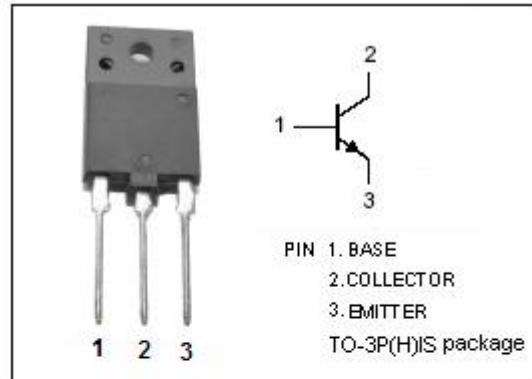


## isc Silicon NPN Power Transistor

**2SC5552**

### DESCRIPTION

- High Breakdown Voltage
- High Switching Speed
- Low Saturation Voltage
- Wide area of safe operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

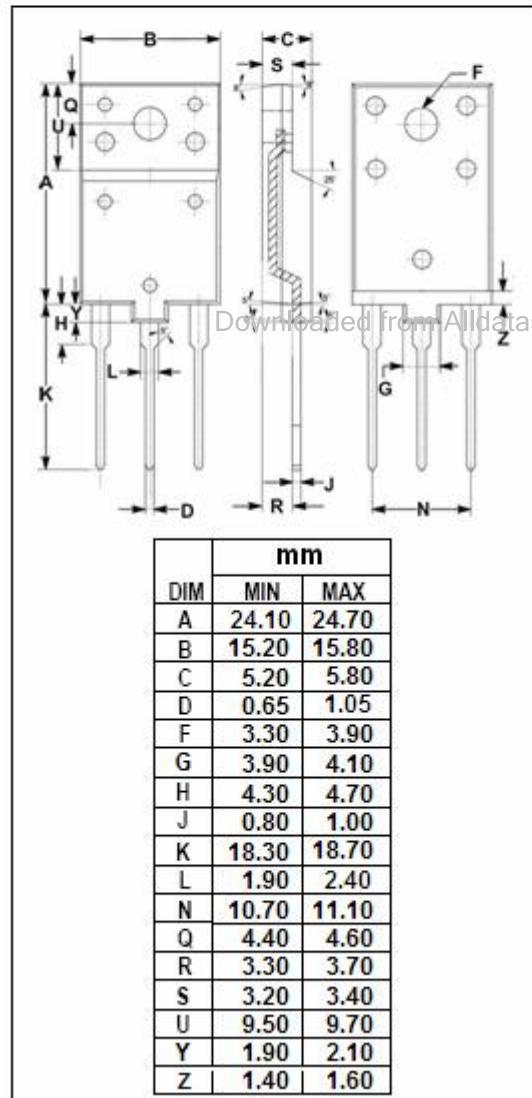


### APPLICATIONS

- Character display horizontal deflection output

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1700	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current- Continuous	16	A
$I_{CM}$	Collector Current- Continuous	30	A
$I_B$	Base Current- Continuous	8	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	65	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC5552****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 8A; I_B= 2A$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 8A; I_B= 2A$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}= 1500V; I_E= 0$			1.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 7V; I_C= 0$			50	uA
$h_{FE}$	DC Current Gain	$I_C= 8A; V_{CE}= 5V$	6		12	
$f_T$	Current-Gain—Bandwidth Product	$I_E= 0.1A ; V_{CE}= 10V$		3		MHz

Switching times

Downloaded from Alldatasheet.com

$t_{stg}$	Storage Time	$I_C= 8A , I_{B1}=2A; I_{B2}= -4A;$			3.0	$\mu s$
$t_f$	Fall Time				0.2	$\mu s$